

### **EMC OPTIMIZED CAN TRANSCEIVER**

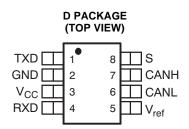
Check for Samples : SN65HVD1050-EP

### **FEATURES**

- Controlled Baseline
  - One Assembly/Test Site, One Fabrication Site
- Enhanced Diminishing Manufacturing Sources (DMS) Support
- Enhanced Product-Change Notification
- Qualification Pedigree (1)
- Improved Replacement for the TJA1050
- High Electromagnetic Immunity (EMI)
- Very Low Electromagnetic Emissions (EME)
- Meets or Exceeds the Requirements of ISO 11898-2
- Bus-Fault Protection of –27 V to 40 V
- Dominant Time-Out Function
- Thermal Shutdown Protection
- Power-Up/Down Glitch-Free Bus Inputs and Outputs
  - High Input Impedance With Low V<sub>CC</sub>
  - Monotonic Outputs During Power Cycling

### **APPLICATIONS**

- Industrial Automation
  - DeviceNET™ Data Buses (Vendor ID #806)
- SAE J2284 High-Speed CAN for Automotive Applications
- SAE J1939 Standard Data Bus Interface
- ISO 11783 Standard Data Bus Interface
- NMEA 2000 Standard Data Bus Interface
- (1) Component qualification in accordance with JEDEC and industry standards to ensure reliable operation over an extended temperature range. This includes, but is not limited to, Highly Accelerated Stress Test (HAST) or biased 85/85, temperature cycle, autoclave or unbiased HAST, electromigration, bond intermetallic life, and mold compound life. Such qualification testing should not be viewed as justifying use of this component beyond specified performance and environmental limits.



## DESCRIPTION/ ORDERING INFORMATION

The SN65HVD1050 meets or exceeds the specifications of the ISO 11898 standard for use in applications employing a controller area network (CAN). The device is also qualified for use in automotive applications in accordance with AEC-Q100. (2)

As a CAN transceiver, this device provides differential transmit capability to the bus and differential receive capability to a CAN controller at signaling rates up to 1 megabit per second (Mbps)<sup>(3)</sup>.

Designed for operation in especially harsh environments, the SN65HVD1050 features cross-wire, overvoltage, and loss of ground protection from -27 V to 40 V, overtemperature protection, a -12-V to 12-V common-mode range, and withstands voltage transients from -200 V to 200 V, according to ISO 7637.

Pin 8 provides for two different modes of operation: high-speed or silent mode. The high-speed mode of operation is selected by connecting S (pin 8) to around.

- (2) The device is available with Q100 qualification as the SN65HVD1050Q (Product Preview).
- (3) The signaling rate of a line is the number of voltage transitions that are made, per second, expressed in the units bps (bits per second).

### ORDERING INFORMATION

PART NUMBER	PACKAGE	MARKED AS	ORDERING NUMBER
SN65HVD1050M	SOIC-8	1050EP	SN65HVD1050MDREP (reel)

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This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### **DESCRIPTION/ORDERING INFORMATION (CONTINUED)**

If a high logic level is applied to the S pin of the SN65HVD1050, the device enters a listen-only silent mode, during which the driver is switched off while the receiver remains fully functional.

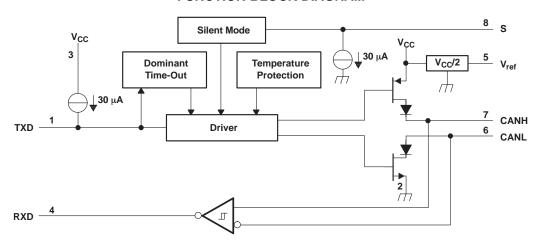
In silent mode, all bus activity is passed by the receiver output to the local protocol controller. When data transmission is required, the local protocol controller reverses this low-current silent mode by placing a logic low on the S pin to resume full operation.

A dominant-time-out circuit in the SN65HVD1050 prevents the driver from blocking network communication with a hardware or software failure. The time-out circuit is triggered by a falling edge on TXD (pin 1). If no rising edge is seen before the time-out constant of the circuit expires, the driver is disabled. The circuit is then reset by the next rising edge on TXD.

V<sub>ref</sub> (pin 5) is available as a V<sub>CC</sub>/2 voltage reference.

The SN65HVD1050M is characterized for operation from -55°C to 125°C.

### **FUNCTION BLOCK DIAGRAM**



### Absolute Maximum Ratings(1)

	-	UNIT
$V_{CC}$	Supply voltage <sup>(2)</sup>	−0.3 V to 7 V
	Voltage range at any bus terminal (CANH, CANL, V <sub>ref</sub> )	–27 V to 40 V
Io	Receiver output current	20 mA
$V_{I}$	Voltage input, transient pulse <sup>(3)</sup> (CANH, CANL)	–200 V to 200 V
$V_{I}$	Voltage input range (TXD, S)	−0.5 V to 6 V
$T_{J}$	Junction temperature	−55°C to 170°C

<sup>(1)</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

<sup>(2)</sup> All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.

<sup>(3)</sup> Tested in accordance with ISO 7637, test pulses 1, 2, 3a, 3b, 5, 6, and 7



### **Electrostatic Discharge Protection**

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		
	Human-Body Model (2)	Bus terminals and GND	±8 kV	
	numan-body woder-	All pins	±4 kV	
Electrostatic discharge <sup>(1)</sup>	Charged-Device Model (3)	All pins	±1.5 kV	
	Machine Model		±200 V	

- All typical values at 25°C
- Tested in accordance with JEDEC Standard 22, Test Method A114-A
  Tested in accordance with JEDEC Standard 22, Test Method C101

**Recommended Operating Conditions** 

	•		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage		4.75	5.25	V
V <sub>I</sub> or V <sub>IC</sub>	Voltage at any bus terminal	(separately or common mode)	-12	12	V
V <sub>IH</sub>	High-level input voltage	TXD, S	2	5.25	V
V <sub>IL</sub>	Low-level input voltage	TXD, S	0	0.8	V
V <sub>ID</sub>	Differential input voltage	Differential input voltage		6	V
	High lovel output ourrent	Driver	-70		mA
I <sub>OH</sub>	High-level output current	Receiver	-2		MA
	Lave lavel avitavit avimont	Driver		70	A
I <sub>OL</sub>	Low-level output current	Receiver		2	mA
T <sub>J</sub>	Junction temperature	See Thermal Characteristics table, 1-Mbps minimum signaling rate with $R_L$ = 54 $\Omega$		150	°C

### **Supply Current**

over recommended operating conditions (unless otherwise noted)

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
		Silent mode	S at V <sub>CC</sub> , V <sub>I</sub> = V <sub>CC</sub>		6	10	·
I <sub>CC</sub> 5-V supply current	Dominant	V <sub>I</sub> = 0 V, 60-Ω load, S at 0 V		50	70	mA	
		Recessive	V <sub>I</sub> = V <sub>CC</sub> , No load, S at 0 V		6	10	1

### **Device Switching Characteristics**

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	MAX	UNIT
t <sub>d(LOOP1)</sub>	Total loop delay, driver input to receiver output, recessive to dominant	S at 0 V Saa Figure 0	90	230	5
t <sub>d(LOOP2)</sub>	Total loop delay, driver input to receiver output, dominant to recessive	S at 0 V, See Figure 9	90	230	ns

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### **Driver Electrical Characteristics**

over recommended operating conditions (unless otherwise noted)

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V	Due output voltage (deminent)	CANH	$V_I = 0 \text{ V}, \text{ S at } 0 \text{ V}, \text{ R}_L = 60 \Omega,$	2.9	3.4	4.5	V
$V_{O(D)}$	Bus output voltage (dominant)	CANL	See Figure 1 and Figure 2	0.8		1.5	V
V <sub>O(R)</sub>	Bus output voltage (recessive)		$V_I = 3 \text{ V, S at } 0 \text{ V, R}_L = 60 \Omega,$ See Figure 1 and Figure 2	2	2.3	3	٧
V	Differential output voltage (domin	ant)	$V_I = 0 \text{ V}, R_L = 60 \Omega, S \text{ at } 0 \text{ V},$ See Figure 1, Figure 2, and Figure 3	1.5		3	V
$V_{OD(D)}$	Differential output voltage (domin	iaiii)	$V_I = 0 \text{ V}, R_L = 45 \Omega, \text{ S at } 0 \text{ V},$ See Figure 1, Figure 2, and Figure 3	1.4		3	V
V <sub>OD(R)</sub>	Differential output voltage (reces	sive)	V <sub>I</sub> = 3 V, S at 0 V, See Figure 1 and Figure 2	-0.012		0.012	V
- ( )			V <sub>I</sub> = 3 V, S at 0 V, No load	-0.5		0.05	
V <sub>OC(ss)</sub>	Steady-state common-mode out	out voltage		2	2.3	3	V
$\Delta V_{OC(ss)}$	Change in steady-state common output voltage	-mode	S at 0 V, See Figure 8		30		mV
I <sub>IH</sub>	High-level input current, TXD inp	ut	V <sub>I</sub> at V <sub>CC</sub>	-2		2	
I <sub>IL</sub>	Low-level input current, TXD inp	ut	V <sub>I</sub> at 0 V	-50		-10	μΑ
I <sub>O(off)</sub>	Power-off TXD output current		V <sub>CC</sub> at 0 V, TXD at 5 V			1	
			V <sub>CANH</sub> = -12 V, CANL open, See Figure 11	-105	-72		
	Chart aircuit ataady atata autaut	arant	V <sub>CANH</sub> = 12 V, CANL open, SeeFigure 11		0.36	1	A
I <sub>OS(ss)</sub>	Short-circuit steady-state output	current	V <sub>CANL</sub> = -12 V, CANH open, See Figure 11	-1	-0.5		mA
	<u> </u>	V <sub>CANL</sub> = 12 V, CANH open, See Figure 11		71	105	1	
Co	Output capacitance		See receiver input capacitance				

<sup>(1)</sup> All typical values are at 25°C, with a 5-V supply.

### **Driver Switching Characteristics**

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
t <sub>PLH</sub>	Propagation delay time, low- to high-level output	S at 0 V Saa Figure 4	25	65	120	20	
t <sub>PHL</sub>	Propagation delay time, high- to low-level output	S at 0 V, See Figure 4	25	45	120	ns	
t <sub>r</sub>	Differential output signal rise time	S at 0 V, See Figure 4		25			
t <sub>f</sub>	Differential output signal fall time	S at 0 V, See Figure 4		50		ns	
t <sub>en</sub>	Enable time from silent mode to dominant	See Figure 7			1	μs	
t <sub>(dom)</sub>	Dominant time-out	↓V <sub>I</sub> , See Figure 10	300	450	700	μs	

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### **Receiver Electrical Characteristics**

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP (1)	MAX	UNIT
$V_{IT+}$	Positive-going input threshold voltage	S at 0 V, See Table 3		800	900	mV
V <sub>IT</sub> _	Negative-going input threshold voltage	S at 0 V, See Table 3	500	650		mV
$V_{\text{hys}}$	Hysteresis voltage (V <sub>IT+</sub> – V <sub>IT-</sub> )		100	125		mV
$V_{OH}$	High-level output voltage	I <sub>O</sub> = -2 mA, See Figure 6	4	4.6		V
V <sub>OL</sub>	Low-level output voltage	I <sub>O</sub> = 2 mA, See Figure 6		0.2	0.4	V
I <sub>I(off)</sub>	Power-off bus input current	CANH or CANL = 5 V, Other pin at 0 V, V <sub>CC</sub> at 0 V, TXD at 0 V		165	250	μΑ
I <sub>O(off)</sub>	Power-off RXD leakage current	V <sub>CC</sub> at 0 V, RXD at 5 V			20	μΑ
Cı	Input capacitance to ground (CANH or CANL)	TXD at 3 V, V <sub>I</sub> = 0.4 sin (4E6πt) + 2.5 V		13		pF
C <sub>ID</sub>	Differential input capacitance	TXD at 3 V, $V_I = 0.4 \sin (4E6\pi t)$		5		pF
R <sub>ID</sub>	Differential input resistance	TXD at 3 V, S at 0 V	30		80	kΩ
R <sub>IN</sub>	Input resistance (CANH or CANL)	TXD at 3 V, S at 0 V	15	30	40	kΩ
R <sub>I(m)</sub>	Input resistance matching [1 – (R <sub>IN (CANH)</sub> / R <sub>IN (CANL)</sub> )] ×100%	$V_{O(CANH)} = V_{O(CANL)}$	-3%	0%	3%	

<sup>(1)</sup> All typical values are at 25 C with a 5-V supply.

### **Receiver Switching Characteristics**

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t <sub>PLH</sub>	Propagation delay time, low- to high-level output	Cat O Van V	60	100	130	9
t <sub>PHL</sub>	Propagation delay time, high- to low-level output	S at 0 V or V <sub>CC</sub> , See Figure 6	45	70	130	ns
t <sub>r</sub>	Output signal rise time	Cat O V an V Can Figure C		8		50
t <sub>f</sub>	Output signal fall time	S at 0 V or V <sub>CC</sub> , See Figure 6		8		ns

### **S-Pin Characteristics**

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$I_{\text{IH}}$	High-level input current	S at 2 V	20	40	70	μΑ
$I_{\text{IL}}$	Low-level input current	S at 0.8 V	5	20	30	μΑ

### **V<sub>ref</sub>-PIN Characteristics**

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{O}$	Reference output voltage	–50 μA < I <sub>O</sub> < 50 μA	0.4 V <sub>CC</sub>	0.5 V <sub>CC</sub>	0.6 V <sub>CC</sub>	V

### **Thermal Characteristics**

over operating free-air temperature range (unless otherwise noted)

	perating free-air temperature range (ur	,					
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
Δ	Junction to Air	Low-K thermal resistance <sup>(1)</sup>	211			°C/W	
$\theta_{JA}$	Junction to All	High-K thermal resistance		131		C/VV	
$\theta_{JB}$	Junction-to-board thermal resistance			53		°C/W	
$\theta_{\text{JC}}$	Junction-to-case thermal resistance			79		°C/W	

Product Folder Link(s): SN65HVD1050-EP

(1) Tested in accordance with the Low-K or High-K thermal metric definitions of EIA/JESD51-3 for leaded surface-mount packages



### **Thermal Characteristics (continued)**

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
D	Average power discinction	$V_{CC}$ = 5 V, T <sub>J</sub> = 27°C, R <sub>L</sub> = 60 $\Omega$ , S at 0 V, Input to TXD a 500-kHz, 50% duty-cycle square wave, C <sub>L</sub> at RXD = 15 pF		112		~^\^/
P <sub>D</sub>	Average power dissipation	$V_{CC}$ = 5.5 V, T <sub>j</sub> = 130°C, R <sub>L</sub> = 45 $\Omega$ , S at 0 V, Input to TXD a 500-kHz, 50% duty-cycle square wave, C <sub>L</sub> at RXD = 15 pF		mW		
	Thermal shutdown temperature			190		°C

### **FUNCTION TABLES**

Table 1. DRIVER

INP	UTS	OUTF	DUC CTATE	
TXD <sup>(1)</sup>	S <sup>(1)</sup>	CANH (1)	CANL (1)	BUS STATE
L	L or Open	Н	L	Dominant
Н	X	Z	Z	Recessive
Open	X	Z	Z	Recessive
X	Н	Z	Z	Recessive

(1) H = high level, L = low level, X = irrelevant, Z = high impedance

**Table 2. RECEIVER** 

DIFFERENTIAL INPUTS V <sub>ID</sub> = V <sub>(CANH)</sub> - V <sub>(CANL)</sub>	OUTPUT RXD (1)	BUS STATE
V <sub>ID</sub> ≥ 0.9 V	L	Dominant
0.5 V < V <sub>ID</sub> < 0.9 V	?	?
V <sub>ID</sub> ≤ 0.5 V	Н	Recessive
Open	Н	Recessive

(1) H = high level, L = low level, X = irrelevant, ? = indeterminate



### PARAMETER MEASUREMENT INFORMATION

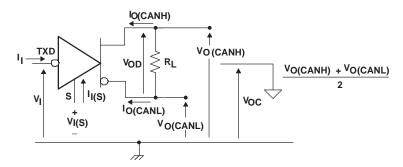


Figure 1. Driver Voltage, Current, and Test Definition

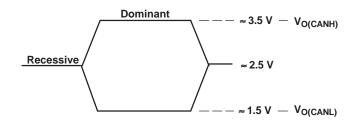


Figure 2. Bus Logic State Voltage Definitions

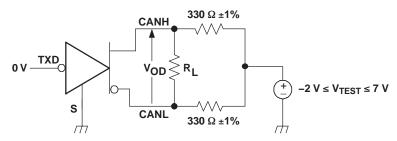


Figure 3. Driver V<sub>OD</sub> Test Circuit

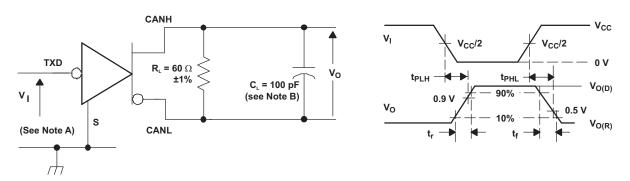


Figure 4. Driver Test Circuit and Voltage Waveforms



### PARAMETER MEASUREMENT INFORMATION (continued)

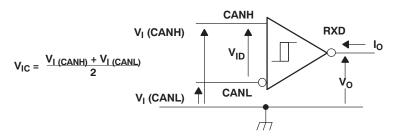
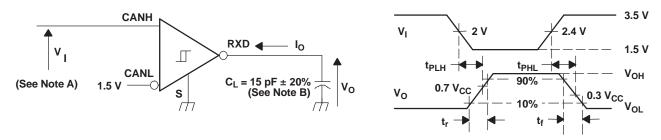


Figure 5. Receiver Voltage and Current Definitions



- A. The input pulse is supplied by a generator having the following characteristics: PRR  $\leq$  125 kHz, 50% duty cycle,  $t_f \leq$  6 ns,  $t_f \leq$  6 ns,  $t_G =$  50  $\Omega$ .
- B. C<sub>L</sub> includes instrumentation and fixture capacitance within ±20%.

Figure 6. Receiver Test Circuit and Voltage Waveforms

**Table 3. Differential Input Voltage Threshold Test** 

	OUT	PUT				
V <sub>CANH</sub>	V <sub>CANL</sub>	V <sub>ID</sub>	R			
–11.1 V	–12 V	900 mV	L			
12 V	11.1 V	900 mV	L	.,		
-6 V	–12 V	6 V	L	V <sub>OL</sub>		
12 V	6 V	6 V	L			
–11.5 V	–12 V	500 mV	Н			
12 V	11.5 V	500 mV	Н			
–12 V	−6 V	6 V	Н	V <sub>OH</sub>		
6 V	12 V	6 V	Н			
Open	Open	X	Н			



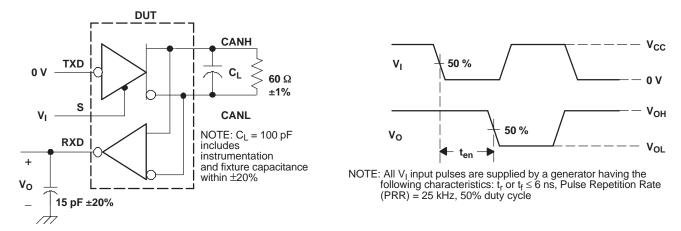
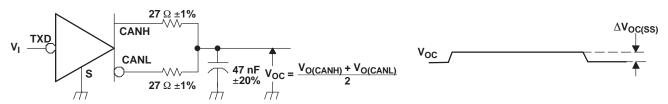
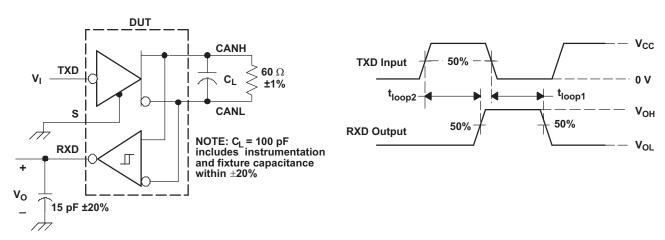


Figure 7. t<sub>en</sub> Test Circuit and Waveforms



NOTE: All  $V_1$  input pulses are from 0 V to  $V_{CC}$  and supplied by a generator having the following characteristics:  $t_r$  or  $t_f \le 6$  ns. Pulse Repetition Rate (PRR) = 125 kHz, 50% duty cycle.

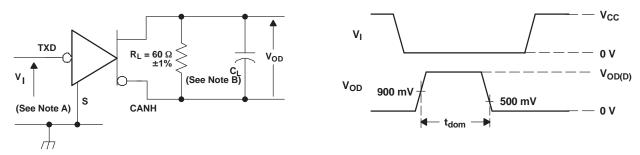
Figure 8. Common-Mode Output Voltage Test and Waveform



A. All  $V_1$  input pulses are from 0 V to  $V_{CC}$  and supplied by a generator having the following characteristics:  $t_r$  or  $t_f \le 6$  ns. Pulse Repetition Rate (PRR) = 125 kHz, 50% duty cycle.

Figure 9. t<sub>(LOOP)</sub> Test Circuit and Waveform





- A. All  $V_1$  input pulses are from 0 V to  $V_{CC}$  and supplied by a generator having the following characteristics:  $t_r$  or  $t_f \le 6$  ns. Pulse Repetition Rate (PRR) = 500 Hz, 50% duty cycle.
- B.  $C_L = 100 \text{ pF}$  includes instrumentation and fixture capacitance within  $\pm 20\%$ .

Figure 10. Dominant Time-Out Test Circuit and Waveforms

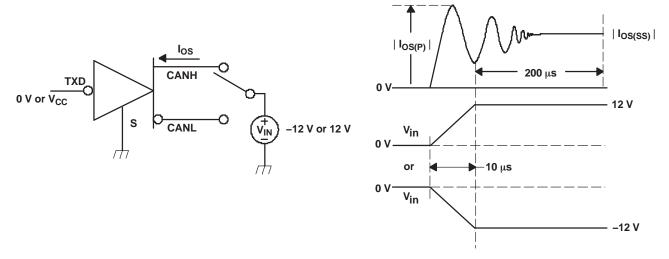


Figure 11. Driver Short-Circuit Current Test and Waveforms



### **DEVICE INFORMATION**

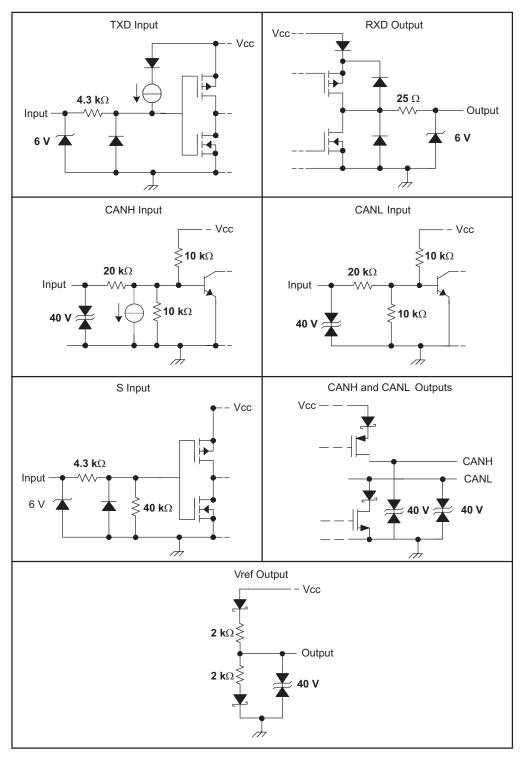
Table 4. Parametric Cross-Reference With the TJA1050

	R HVD1050
$\begin{array}{c cccc} V_{IL} & Low-level input voltage \\ \hline I_{IH} & High-level input current \\ \hline I_{IL} & Low-level input current \\ \hline \\ \textbf{Bus Section} \\ \hline I_{LI} & Power-off bus input current \\ \hline I_{O(SC)} & Short-circuit output current \\ \hline V_{O(dom)} & Dominant output voltage \\ \hline V_{i(dif)(th)} & Differential input voltage \\ \hline V_{i(dif)(hys)} & Differential input hysteresis \\ \hline \end{array}$	
$\begin{array}{ccc} I_{lH} & \text{High-level input current} \\ I_{lL} & \text{Low-level input current} \\ \hline \textbf{Bus Section} \\ I_{LI} & \text{Power-off bus input current} \\ I_{O(SC)} & \text{Short-circuit output current} \\ V_{O(dom)} & \text{Dominant output voltage} \\ V_{i(dif)(th)} & \text{Differential input voltage} \\ V_{i(dif)(hys)} & \text{Differential input hysteresis} \\ \end{array}$	Recommended V <sub>IH</sub>
$\begin{array}{lll} I_{IL} & \text{Low-level input current} \\ \hline \textbf{Bus Section} \\ I_{LI} & \text{Power-off bus input current} \\ I_{O(SC)} & \text{Short-circuit output current} \\ V_{O(dom)} & \text{Dominant output voltage} \\ V_{i(dif)(th)} & \text{Differential input voltage} \\ V_{i(dif)(hys)} & \text{Differential input hysteresis} \\ \hline \end{array}$	Recommended V <sub>IL</sub>
$\begin{tabular}{l l l l l l l l l l l l l l l l l l l $	Driver I <sub>IH</sub>
$\begin{array}{c c} I_{LI} & Power-off bus input curren \\ I_{O(SC)} & Short-circuit output current \\ V_{O(dom)} & Dominant output voltage \\ V_{i(dif)(th)} & Differential input voltage \\ V_{i(dif)(hys)} & Differential input hysteresis \\ \end{array}$	Driver I <sub>IL</sub>
$\begin{array}{c} I_{O(SC)} & Short\text{-circuit output current} \\ V_{O(dom)} & Dominant output voltage \\ V_{i(dif)(th)} & Differential input voltage \\ V_{i(dif)(hys)} & Differential input hysteresis \\ \end{array}$	
$\begin{array}{c} V_{O(dom)} & \text{Dominant output voltage} \\ V_{i(dif)(th)} & \text{Differential input voltage} \\ V_{i(dif)(hys)} & \text{Differential input hysteresis} \end{array}$	t Receiver I <sub>I(off)</sub>
$ \begin{array}{ll} V_{i(dif)(th)} & \text{Differential input voltage} \\ V_{i(dif)(hys)} & \text{Differential input hysteresis} \end{array} $	Driver I <sub>OS(SS)</sub>
V <sub>i(dif)(hys)</sub> Differential input hysteresis	Driver V <sub>O(D)</sub>
	Receiver V <sub>IT</sub> and recommended V <sub>ID</sub>
V <sub>O(reces)</sub> Recessive output voltage	Receiver V <sub>hys</sub>
· · · · · · · · · · · · · · · · · · ·	Driver V <sub>O(R)</sub>
V <sub>O(dif)(bus)</sub> Differential bus voltage	Driver V <sub>OD(D)</sub> and V <sub>OD(R)</sub>
R <sub>i(cm)</sub> CANH, CANL input resista	nce Receiver R <sub>IN</sub>
R <sub>i(dif)</sub> Differential input resistance	e Receiver R <sub>ID</sub>
R <sub>i(cm) (m)</sub> Input resistance matching	Receiver R <sub>I (m)</sub>
C <sub>I</sub> Input capacitance to groun	d Receiver C <sub>I</sub>
C <sub>i(dif)</sub> Differential input capacitan	ce Receiver C <sub>ID</sub>
Receiver Section	
I <sub>OH</sub> High-level output current	Recommended I <sub>OH</sub>
I <sub>OL</sub> Low-level output current	Recommended I <sub>OL</sub>
V <sub>ref</sub> -Pin Section	
V <sub>ref</sub> Reference output voltage	Vo
Timing Section	
t <sub>d(TXD-BUSon)</sub> Delay TXD to bus active	Driver t <sub>PLH</sub>
t <sub>d(TXD-BUSoff)</sub> Delay TXD to bus inactive	Driver t <sub>PHL</sub>
t <sub>d(BUSon-RXD)</sub> Delay bus active to RXD	Receiver t <sub>PHL</sub>
$t_{\text{d(BUSoff-RXD)}}$ Delay bus inactive to RXD	Receiver t <sub>PLH</sub>
$t_{d(TXD\text{-BUSon})} + t_{d(BUSon\text{-RXD})}$	Device t <sub>LOOP1</sub>
$t_{d(TXD\text{-BUSoff})} + t_{d(BUSoff\text{-RXD})}$	Device t <sub>LOOP2</sub>
t <sub>dom(TXD)</sub> Dominant time-out	Driver t <sub>(dom)</sub>
S-Pin Section	
V <sub>IH</sub> High-level input voltage	Recommended V <sub>IH</sub>
V <sub>IL</sub> Low-level input voltage	Recommended V <sub>IL</sub>
I <sub>IH</sub> High-level input current	I <sub>IH</sub>
I <sub>IL</sub> Low-level input current	I <sub>IL</sub>

<sup>(1)</sup> From TJA1050 Product Specification, Philips Semiconductors, 2002 May 16



### **Equivalent Input and Output Schematic Diagrams**

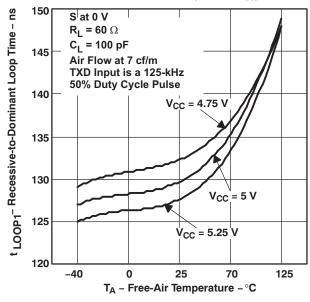




### TYPICAL CHARACTERISTICS

### RECESSIVE-TO-DOMINANT LOOP TIME

### FREE-AIR TEMPERATURE (Across V<sub>CC</sub>)



### Figure 12.

## SUPPLY CURRENT (RMS) vs

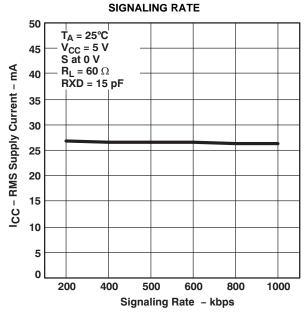


Figure 14.

# DOMINANT-TO-RECESSIVE LOOP TIME vs FREE-AIR TEMPERATURE (Across V<sub>CC</sub>)

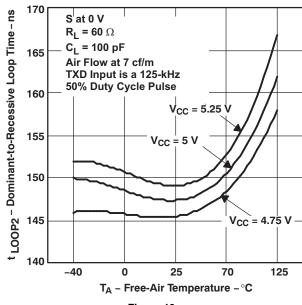


Figure 13.

# DRIVER LOW-LEVEL OUTPUT VOLTAGE vs LOW-LEVEL OUTPUT CURRENT

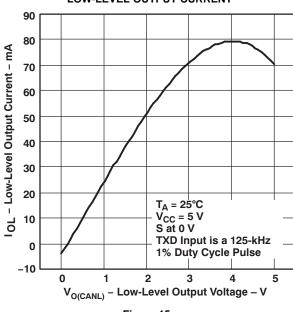


Figure 15.



### **TYPICAL CHARACTERISTICS (continued)**

### DRIVER HIGH-LEVEL OUTPUT VOLTAGE VS HIGH-LEVEL OUTPUT CURRENT -80 $T_A = 25^{\circ}C$ $V_{CC} = 5 V$ IOH - High-Level Output Current - mA Sat 0 V -70 TXD Input is a 125-kHz 1% Duty Cycle Pulse -60 -50 -40 -30 -20 -10 -0 0 2 3 4 5 V<sub>O(CANH)</sub> - High-Level Output Voltage - V

# DRIVER OUTPUT CURRENT vs SUPPLY VOLTAGE

Figure 16.

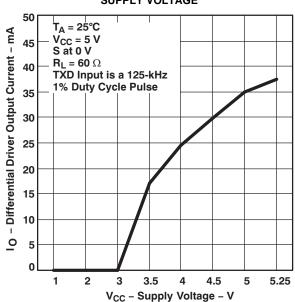
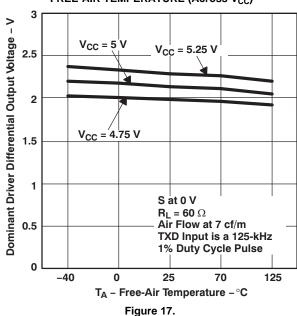


Figure 18.

# DRIVER DIFFERENTIAL OUTPUT VOLTAGE vs FREE-AIR TEMPERATURE (Across V<sub>CC</sub>)



# RECEIVER OUTPUT VOLTAGE vs DIFFERENTIAL INPUT VOLTAGE

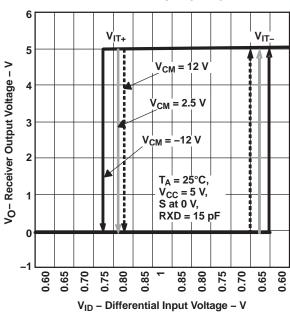
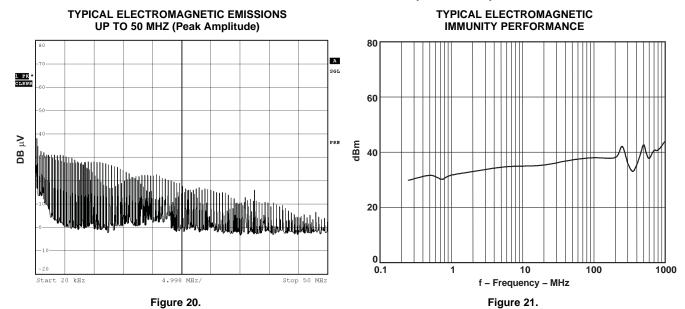


Figure 19.



### **TYPICAL CHARACTERISTICS (continued)**



### PACKAGE OPTION ADDENDUM

www.ti.com 22-Oct-2009

### PACKAGING INFORMATION

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins I	Package Qty	Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
SN65HVD1050MDREP	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65HVD1050MDREPG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
V62/07608-01XE	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <a href="http://www.ti.com/productcontent">http://www.ti.com/productcontent</a> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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### OTHER QUALIFIED VERSIONS OF SN65HVD1050-EP:

Catalog: SN65HVD1050

• Automotive: SN65HVD1050-Q1

NOTE: Qualified Version Definitions:

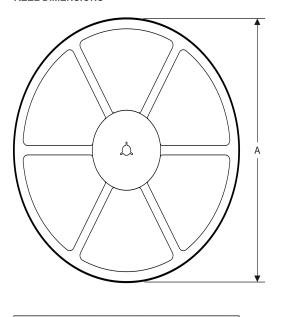
- Catalog TI's standard catalog product
- Automotive Q100 devices qualified for high-reliability automotive applications targeting zero defects

### PACKAGE MATERIALS INFORMATION

www.ti.com 14-Jul-2012

### TAPE AND REEL INFORMATION

### **REEL DIMENSIONS**



### **TAPE DIMENSIONS**



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### TAPE AND REEL INFORMATION

### \*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65HVD1050MDREP	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

**PACKAGE MATERIALS INFORMATION** 

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### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65HVD1050MDREP	SOIC	D	8	2500	367.0	367.0	35.0

## D (R-PDSO-G8)

### PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



## D (R-PDSO-G8)

## PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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